



TH9030

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TH9030** is Designed for General Purpose Power oscillator Amplifier Applications up to 2.3 GHz.

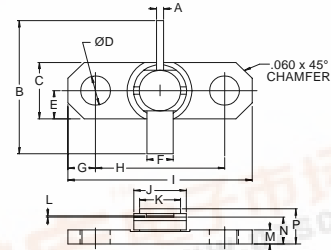
FEATURES:

- Common Collector
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	600 mA
V_{CEO}	20 V
V_{CB0}	45 V
V_{EBO}	3.0 V
P_{DISS}	7.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	25 °C/W

PACKAGE STYLE .250 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E		.125 / 3.18
F	.110 / 2.79	.117 / 2.97
G		.117 / 2.97
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CB0}	V _{CB} = 30 V			.25	mA
I_{EBO}	V _{EB} = 2.0 V			.25	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	15		120	---
C_{OB}	V _{CB} = 20 V f = 1.0 MHz		1.5	2.5	pF
P_{OSC}	V _{CE} = 18 V I _E = 250 mA f = 2.3 GHz		1.6		W

